SSC8L3A30GN6

Dual N-Channel Enhancement Mode MOSFET

➢ Features

V_{DS}	V_{GS}	$R_{DS(ON)}$ Typ.	I_D
100V	±20V	18mΩ@10V	38A
		22mΩ@4V5	

➢ Description

This device is N-Channel enhancement MOSFET. Uses SGT technology and design to provide excellent RDSON with low gate charge. This device is suitable for use in DC-DC conversion, power switch and charging circuit.

100% UIS + ΔVDS + Rg Tested!

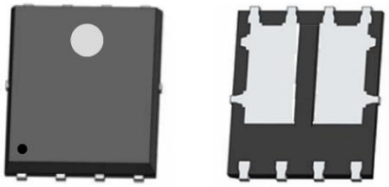
➢ Applications

- Motor Drive Control
- DCDC Conversion
- Power Supplies
- Synchronous Rectification

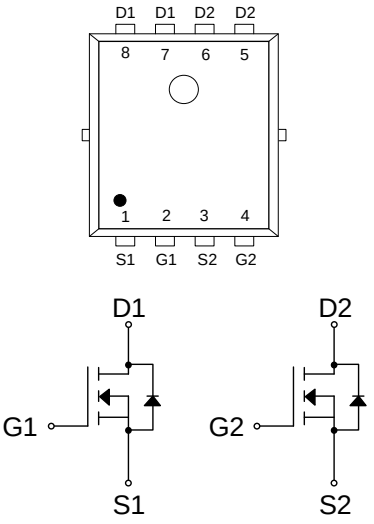
➢ Ordering Information

Device	Package	Shipping
SSC8L3A30GN6	PDFN5X6-8L	5000/Reel

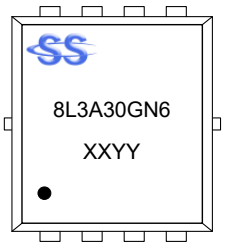
➢ Pin Configuration



PDFN5X6-8L



Pin Configuration (Top View)



Marking

(XXYY: Internal Traceability Code)

➢ Absolute Maximum Ratings (T_A=25℃ unless otherwise noted)

Symbol	Parameter		Ratings	Unit
V_{DSS}	Drain-to-Source Voltage		100	V
V_{GSS}	Gate-to-Source Voltage		±20	V
I_D	Continuous Drain Current [d]	T_C=25℃	38	A
		T_C=100℃	21	
I_{DSM}	Continuous Drain Current [a]	T_A=25℃	8.5	A
		T_A=70℃	6.2	
I_{DM}	Pulsed Drain Current [b]		152	A
P_D	Power Dissipation [c]	T_C=25℃	41	W
		T_C=100℃	16	
P_{DSM}	Power Dissipation [a]	T_A=25℃	2.1	W
		T_A=70℃	1.3	
I_{AS}	Avalanche Current [b] L=0.5mH Single Pulse		7	A
E_{AS}	Avalanche Energy [b] L=0.5mH Single Pulse		12.2	mJ
T_J	Operation junction temperature		-55~150	℃
T_{STG}	Storage temperature range		-55~150	

➢ Thermal Resistance Ratings (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Ratings	Unit
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance [a]	60	℃/W
$R_{\theta JC}$	Junction-to-Case Thermal Resistance	3	

Note:

a. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in^2 FR-4 board with 2oz.copper, in a still air environment with T_A=25℃.The value in any given application depends on the user is specific board design. The power dissipation is based on the t≤10s thermal resistance rating.

b. Repetitive rating, pulse width limited by junction temperature.

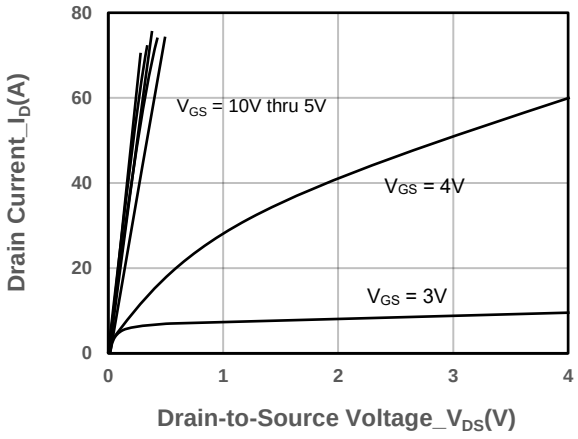
c. The power dissipation P_D is based on $T_{J(MAX)}$=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.

d. The maximum current rating is package limited.

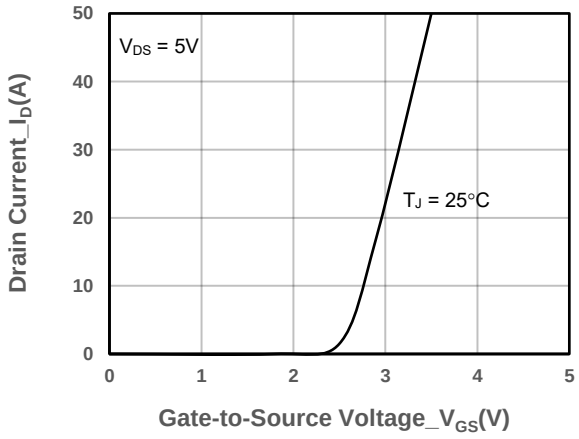
➢ Electrical Characteristics (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	100			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250uA	1	1.8	2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = 10V, I_D = 20A		18	23	mΩ
		V_{GS} = 4.5V, I_D = 10A		22	28	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 100V, V_{GS} = 0V			1	μA
Gate-Source Leak Current	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
Transconductance	G_{FS}	V_{DS} = 5V, I_D = 10A		15		S
Forward Voltage	V_{SD}	V_{GS} = 0V, I_S = 10A		0.8	1.3	V
Gate Resistance	R_G	V_{DS} = 0V, f = 1MHz		0.63		Ω
Input Capacitance	C_{ISS}	V_{DS} = 50V, V_{GS} = 0V, f = 1MHz		680		pF
Output Capacitance	C_{OSS}			255		
Reverse Transfer Capacitance	C_{RSS}			6.3		
Total Gate Charge	Q_G	V_{GS} = 10V, V_{DS} = 50V, I_D = 20A		22		nC
Gate to Source Charge	Q_{GS}			3.8		
Gate to Drain Charge	Q_{GD}			4.9		
Turn-on Delay Time	$T_{D(ON)}$	V_{GS} = 10V, V_{DS} = 50V, I_D = 20A, R_G = 3Ω		21		ns
Rise Time	T_r			14		
Turn-off Delay Time	$T_{D(OFF)}$			23		
Fall Time	T_f			6.4		
Diode Recovery Time	T_{rr}	I_F=20A, di/dt=100A/us		28		ns
Diode Recovery Charge	Q_{rr}	I_F=20A, di/dt=100A/us		31		nC

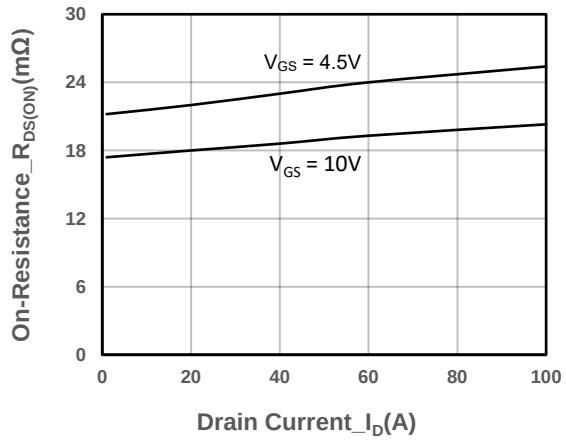
➢ Typical Performance Characteristics (T_A=25℃ unless otherwise noted)



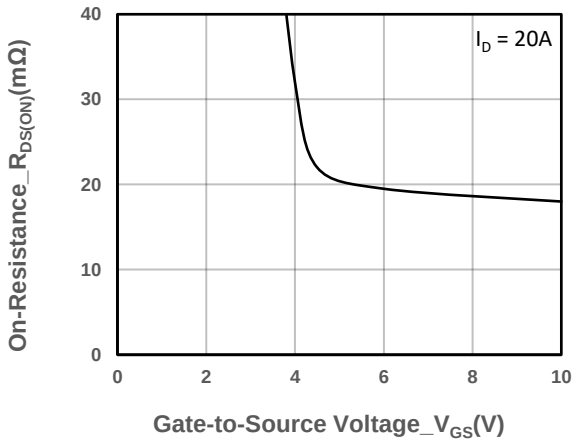
Output Characteristics



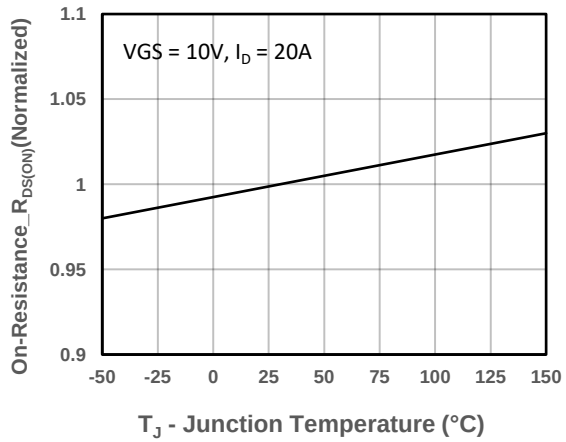
Transfer Characteristics



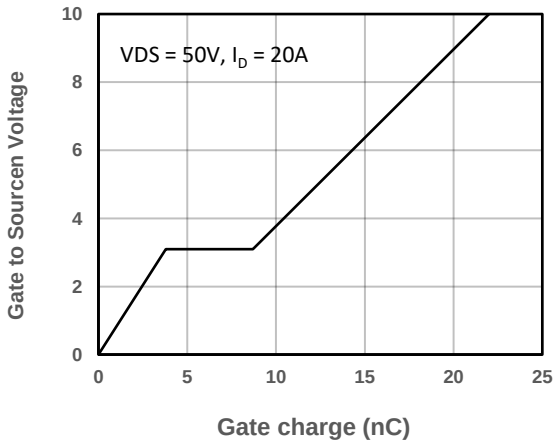
On-Resistance vs. Drain Current and Gate Voltag



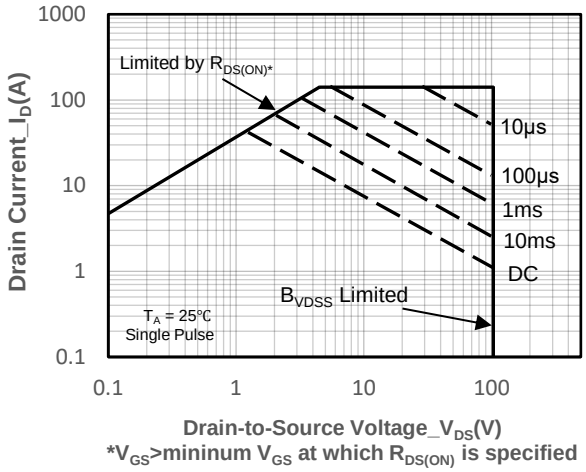
On-Resistance vs. Gate-to-Source Voltage



On-Resistance vs. Junction Temperature

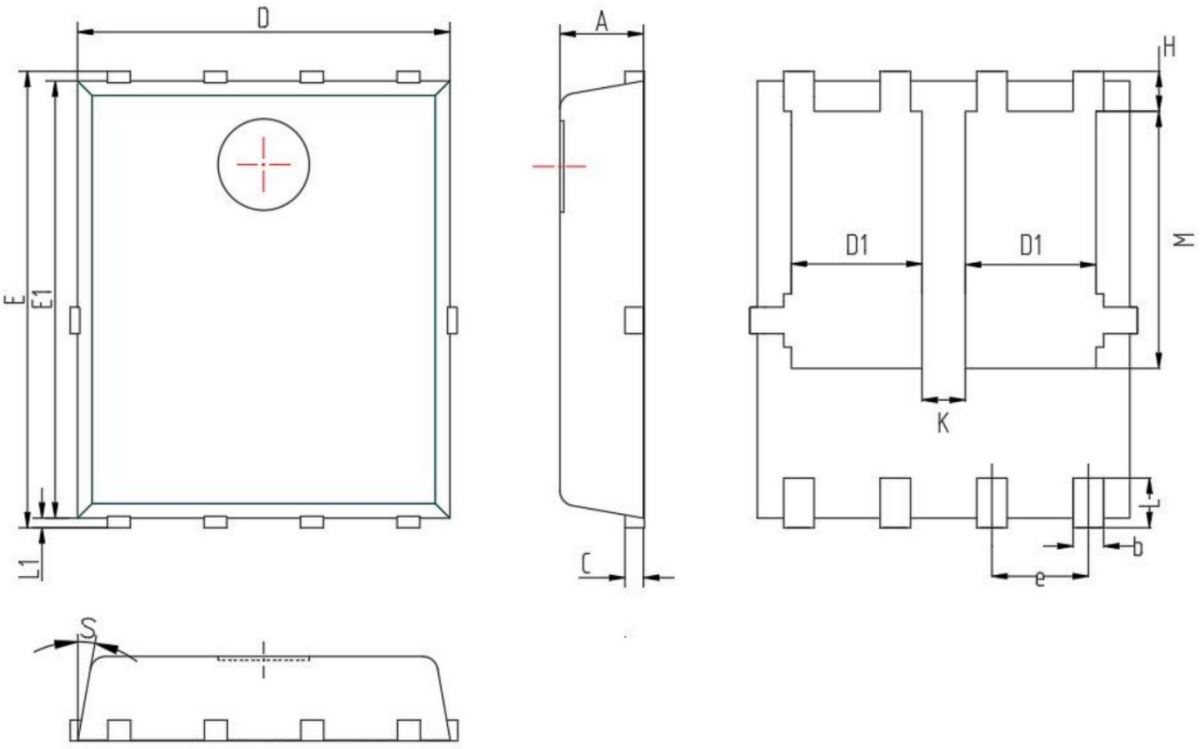


Gate-Source Voltage vs. Gate charge



Safe Operating Area vs. Junction-to-Ambient

➢ Package Information



Symbol	MILL IMETER		
	Min	Nom	Max
A	0.9	1.10	1.20
b	0.25	0.30	0.5
C	0.20	0.25	0.35
D	4.80	5.00	5.20
D1	1.50	1.70	1.80
E	5.90	6.00	6.30
E1	5.60	5.75	5.90
e	1.27BSC		
H	0.48	0.58	0.80
K	0.50	0.60	0.70
L	0.50	0.60	0.84
L1	0.10	0.15	0.30
M	3.30	3.48	3.67
S	12° BSC		

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